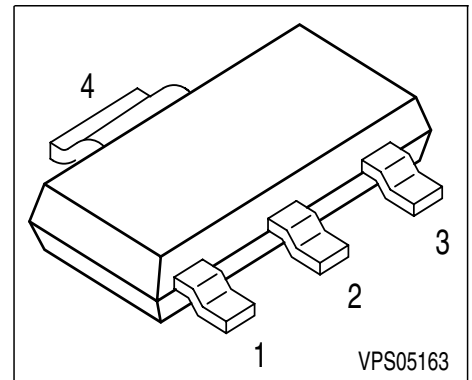


NPN Silicon Switching Transistor

- High DC current gain: 0.1mA to 100mA
- Low collector-emitter saturation voltage
- Complementary type: PZT 3906 (PNP)



Type	Marking	Pin Configuration				Package
PZT 3904	ZT 3904	1 = B	2 = C	3 = E	4 = C	SOT-223

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	40	V
Collector-base voltage	V_{CBO}	60	
Emitter-base voltage	V_{EBO}	6	
DC collector current	I_C	200	mA
Total power dissipation, $T_S = 72^\circ\text{C}$	P_{tot}	1.5	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Junction ambient ¹⁾	R_{thJA}	≤ 122	K/W
Junction - soldering point	R_{thJS}	≤ 52	

1) Package mounted on pcb 40mm x 40mm x 1.5mm / 6cm² Cu

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage $I_C = 1\text{ mA}$, $I_B = 0$	$V_{(BR)CEO}$	40	-	-	V
Collector-base breakdown voltage $I_C = 10\text{ }\mu\text{A}$, $I_B = 0$	$V_{(BR)CBO}$	60	-	-	
Emitter-base breakdown voltage $I_E = 10\text{ }\mu\text{A}$, $I_C = 0$	$V_{(BR)EBO}$	6	-	-	
Collector cutoff current $V_{CB} = 30\text{ V}$, $I_E = 0$	I_{CBO}	-	-	50	nA
Collector-emitter cutoff current $V_{CE} = 30\text{ V}$, $-V_{BE} = 0.5\text{ V}$	I_{CEV}	-	-	50	
Base-emitter cutoff current $V_{CE} = 30\text{ V}$, $-V_{BE} = 0.5$	I_{BEV}	-	-	50	
DC current gain 1) $I_C = 0.1\text{ mA}$, $V_{CE} = 1\text{ V}$ $I_C = 1\text{ mA}$, $V_{CE} = 1\text{ V}$ $I_C = 10\text{ mA}$, $V_{CE} = 1\text{ V}$ $I_C = 50\text{ mA}$, $V_{CE} = 1\text{ V}$ $I_C = 100\text{ mA}$, $V_{CE} = 1\text{ V}$	h_{FE}	40 70 100 60 30	- - - - -	- - 300 - -	-
Collector-emitter saturation voltage1) $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat}	- -	- -	0.2 0.3	
Base-emitter saturation voltage 1) $I_C = 100\text{ mA}$, $I_B = 1\text{ mA}$ $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat}	- -	- -	0.85 0.9	

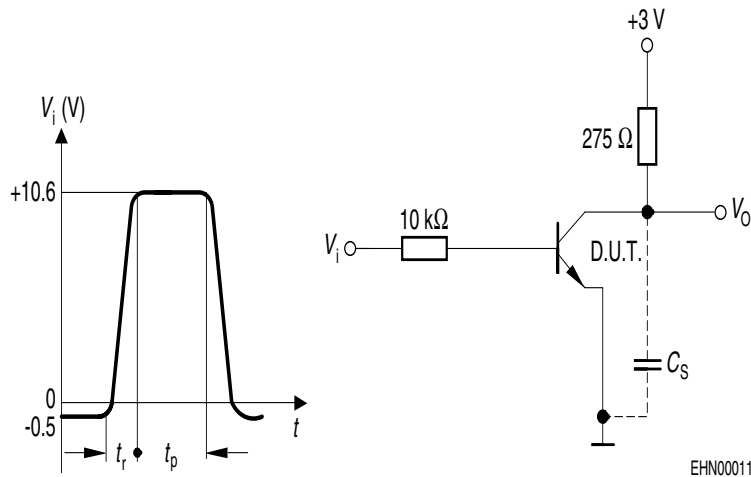
1) Pulse test: $t \leq 300\mu\text{s}$, $D = 2\%$

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency $I_C = 10\text{ mA}$, $V_{CE} = 20\text{ V}$, $f = 100\text{ MHz}$	f_T	300	-	-	MHz
Collector-base capacitance $V_{CB} = 5\text{ V}$, $f = 1\text{ MHz}$	C_{cb}	-	-	4	pF
Emitter-base capacitance $V_{EB} = 0.5\text{ V}$, $f = 1\text{ MHz}$	C_{eb}	-	-	8	
Noise figure $I_C = 100\text{ }\mu\text{A}$, $V_{CE} = 5\text{ V}$, $R_S = 1\text{ k}\Omega$, $f = 10\text{Hz to } 15.7\text{kHz}$,	F	-	-	5	dB
Short-circuit input impedance $I_C = 1\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1\text{ kHz}$	h_{11e}	1	-	10	k Ω
Open-circuit reverse voltage transf.ratio $I_C = 1\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1\text{ kHz}$	h_{12e}	0.5	-	8	10 ⁻⁴
Short-circuit forward current transf.ratio $I_C = 1\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1\text{ kHz}$	h_{21e}	100	-	400	-
Open-circuit output admittance $I_C = 1\text{ mA}$, $V_{CE} = 10\text{ V}$, $f = 1\text{ kHz}$	h_{22e}	1	-	40	μS
Delay time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$, $V_{BE(\text{off})} = 0.5\text{ V}$	t_d	-	-	35	ns
Rise time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1} = 1\text{ mA}$, $V_{BE(\text{off})} = 0.5\text{ V}$	t_r	-	-	35	
Storage time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1}=I_{B2} = 1\text{mA}$	t_{stg}	-	-	200	
Fall time $V_{CC} = 3\text{ V}$, $I_C = 10\text{ mA}$, $I_{B1}=I_{B2} = 1\text{mA}$	t_f	-	-	50	

Switching Times

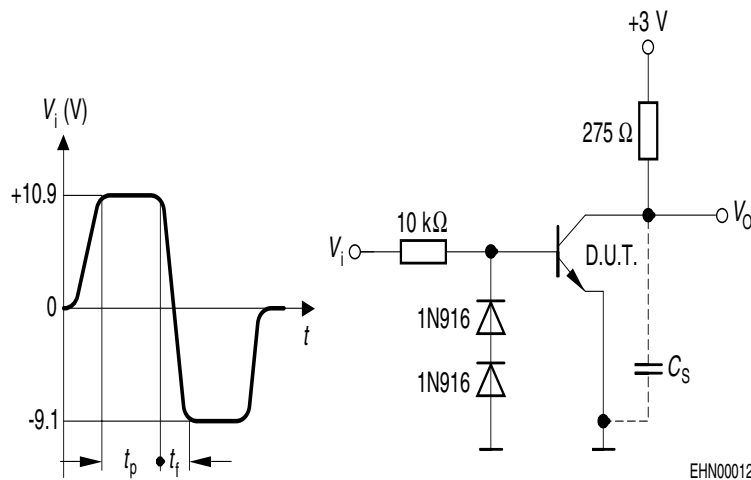
Turn-on time when switched from + $V_{BEoff} = 0.5V$ to - $V_{BEon} = 10.6V$, - $I_{Con} = 10mA$
 - $I_{Bon} = 1mA$



Input waveform; $t_r < 1ns$; $t_p = 300 ns$
 $\delta = 0.002$

Delay and rise time test circuit; total shunt capacitance of test jig and connectors
 $C_s < 4pF$; scope impedance = $10M\Omega$

Turn-off time $I_{Con} = 10mA$; $I_{Bon} = 1mA$

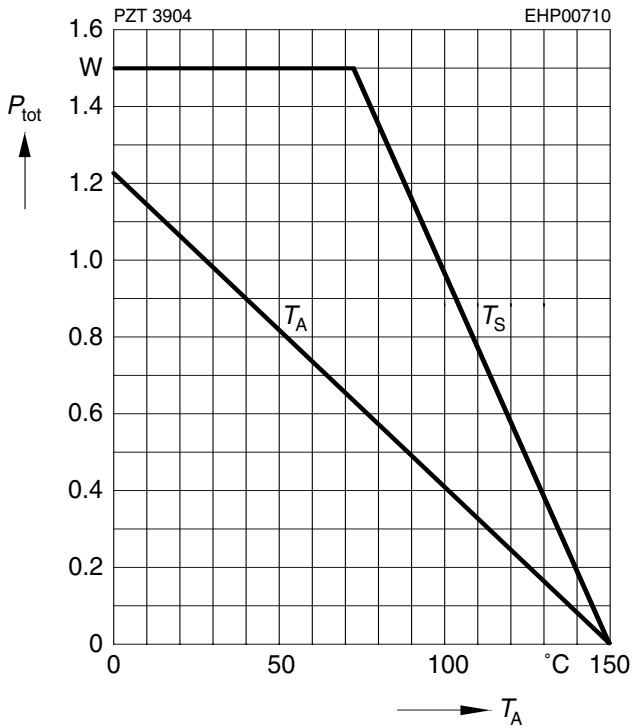


Input waveform; $t_r < 1ns$; $10 \mu s < t_p \leq 500 \mu s$
 $\delta = 0.02$

Storage and fall time test circuit; total shunt capacitance of test jig and connectors
 $C_s < 4pF$; scope impedance = $10M\Omega$

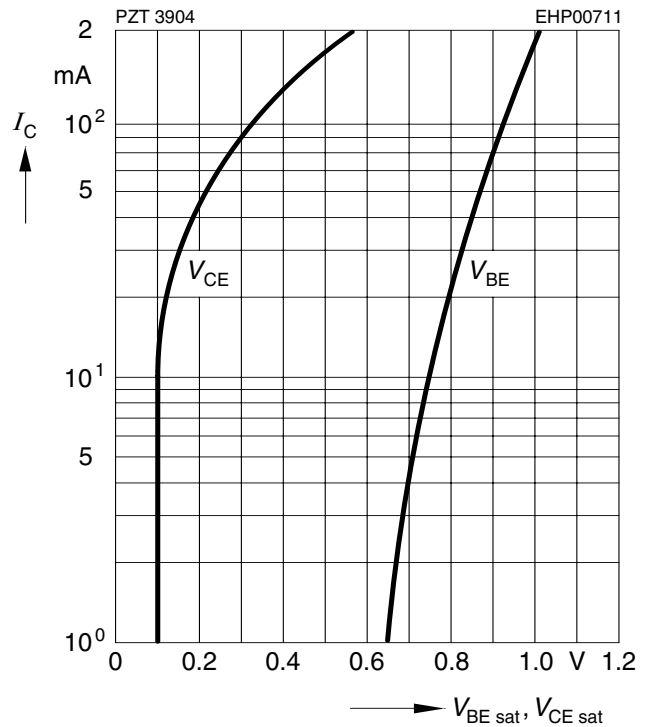
Total power dissipation $P_{\text{tot}} = f(T_A^*; T_S)$

* Package mounted on epoxy



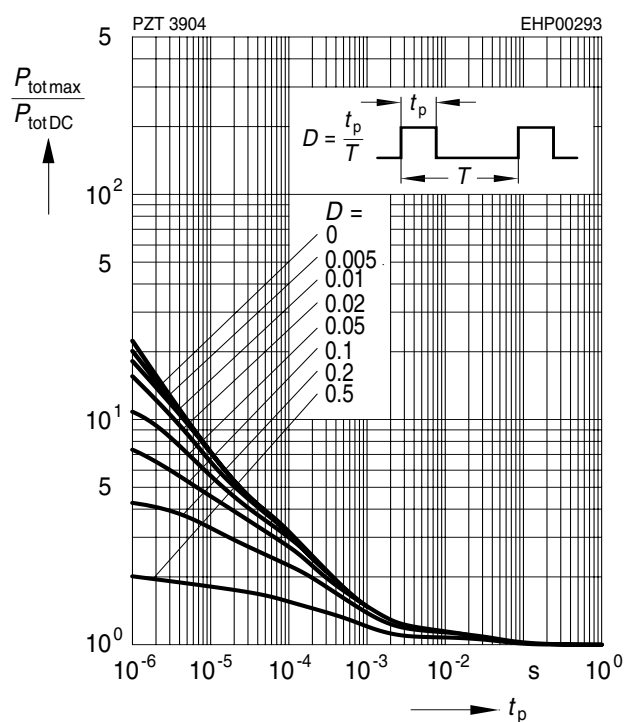
Saturation voltage $I_C = f(V_{\text{BEsat}}, V_{\text{CEsat}})$

$h_{\text{FE}} = 10$



Permissible pulse load

$P_{\text{totmax}} / P_{\text{totDC}} = f(t_p)$



DC current gain $h_{\text{FE}} = f(I_C)$

$V_{\text{CE}} = 10\text{V}$, normalized

